



PJP75N75

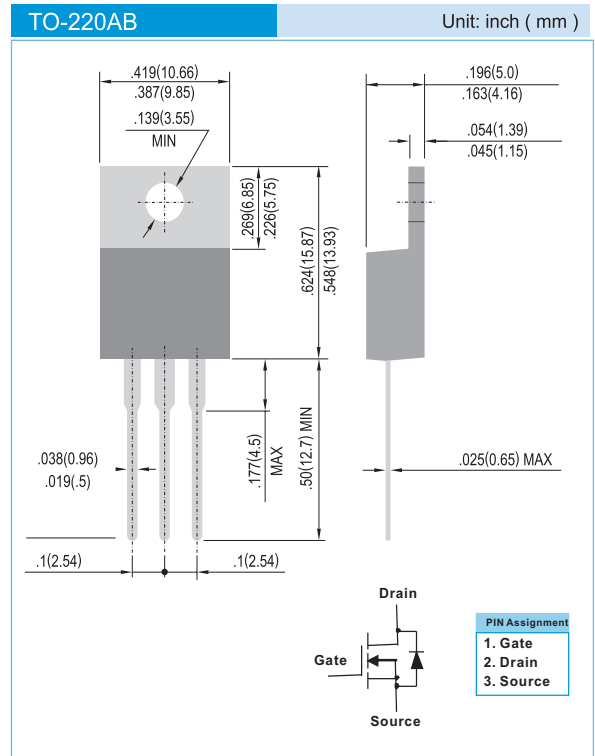
75V N-Channel Enhancement Mode MOSFET

FEATURES

- $R_{DS(ON)}$, V_{GS} @ 10V, I_{DS} @ 30A=12m Ω
- $R_{DS(ON)}$, V_{GS} @ 4.5V, I_{DS} @ 30A=18m Ω
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Specially Designed for Converters and Power Motor Controls
- Fully Characterized Avalanche Voltage and Current
- Pb free product : 99% Sn above can meet RoHS environment substance directive request

MECHANICAL DATA

- Case: TO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750, Method 2026
- Marking : P75N75



Maximum RATINGS and Thermal Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	75	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	75	A
Pulsed Drain Current ¹⁾	I_{DM}	350	A
Maximum Power Dissipation	P_D	105 62.5	W
		$T_A=25^{\circ}\text{C}$ $T_A=75^{\circ}\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^{\circ}\text{C}$
Avalanche Energy with Single Pulse $I_D=41\text{A}, V_{DD}=25\text{V}, L=0.5\text{mH}$	E_{AS}	420	mJ
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.2	$^{\circ}\text{C/W}$
Junction-to Ambient Thermal Resistance(PCB mounted) ²⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Note: 1. Maximum DC current limited by the package

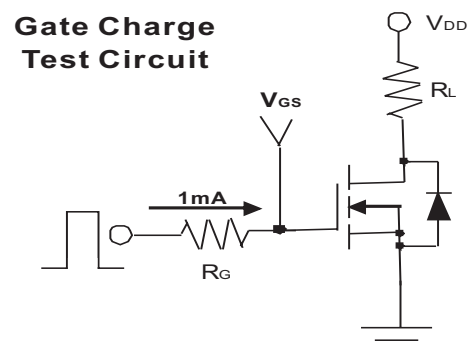
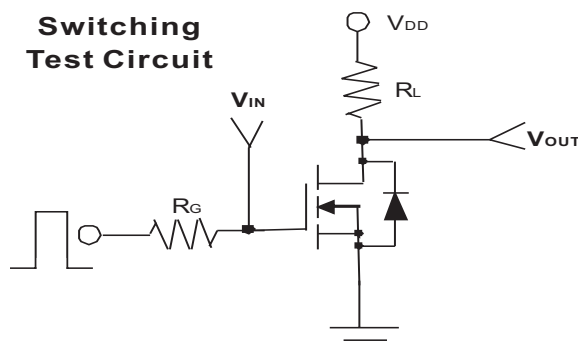
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ELECTRICAL CHARACTERISTICS

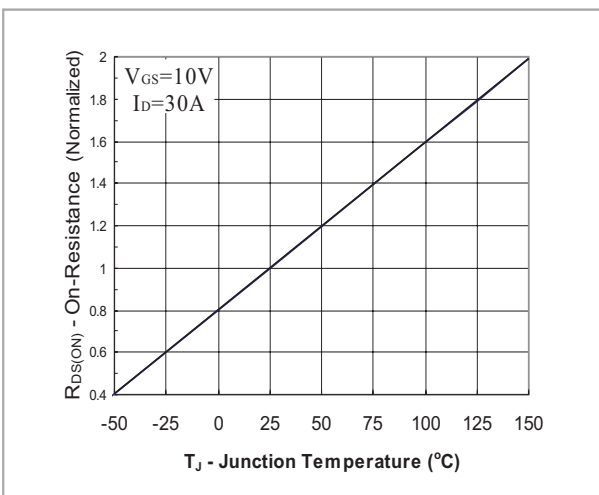
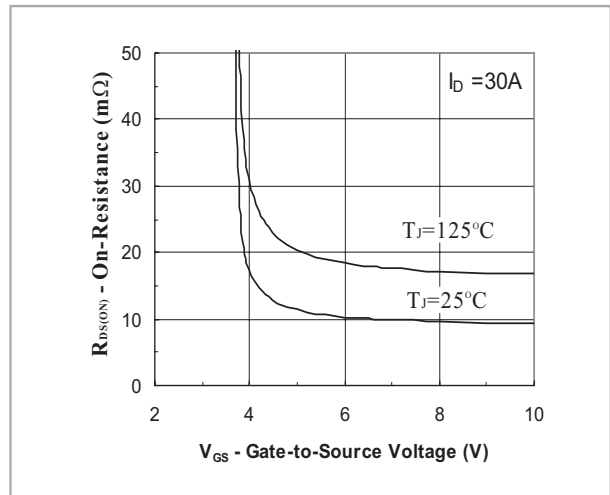
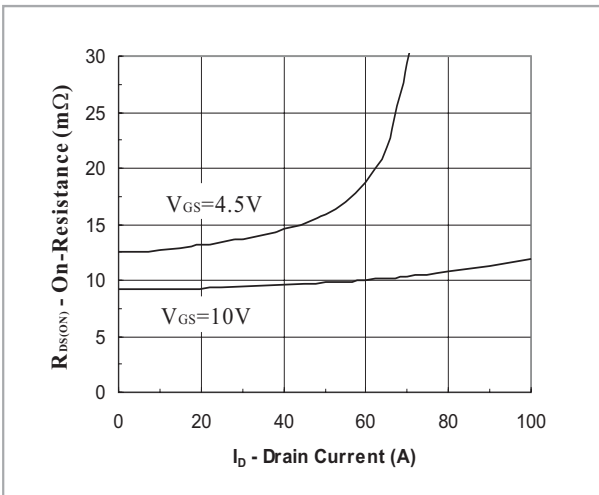
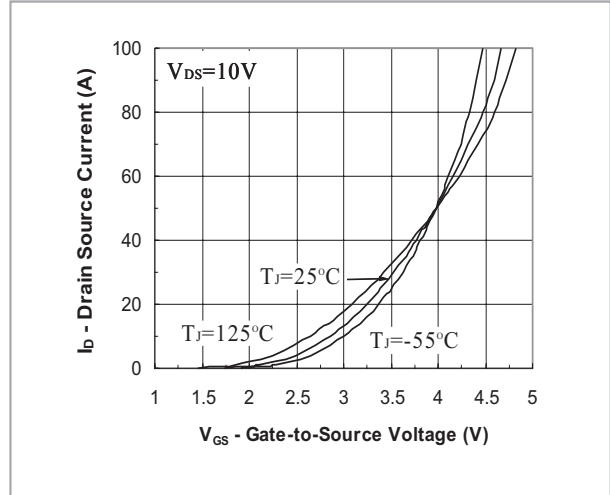
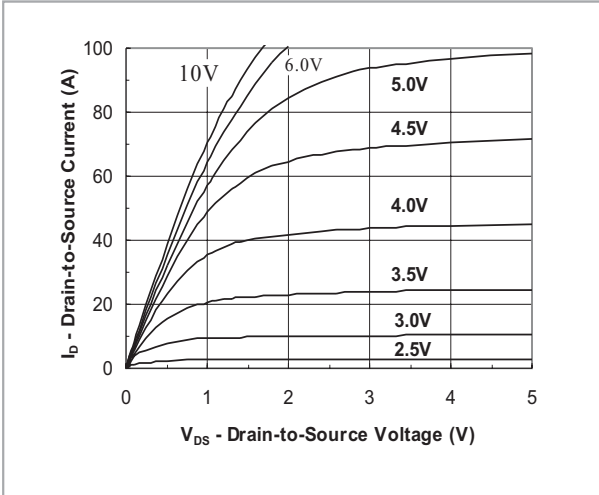
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	75	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=30A$	-	14.2	18	mΩ
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=30A$	-	9.5	12	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=15A$	30	-	-	S
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=30A, V_{GS}=5V$	-	33	-	nC
			-	63.5	-	
Gate-Source Charge	Q_{gs}	$V_{DS}=30V, I_D=30A, V_{GS}=10V$	-	9.2	-	
Gate-Drain Charge	Q_{gd}		-	15	-	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=30V, R_L=15\Omega, I_b=2A, V_{GEN}=10V, R_G=2.5\Omega$	-	18.5	20	ns
Turn-On Rise Time	t_{rr}		-	16.5	14	
Turn-Off Delay Time	$t_{d(off)}$		-	52	68	
Turn-Off Fall Time	t_f		-	8.1	12	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	3200	-	pF
Output Capacitance	C_{oss}		-	260	-	
Reverse Transfer Capacitance	C_{rss}		-	210	-	
Source-Drain Diode						
Max. Diode Forward Current	I_s	-	-	-	75	A
Diode Forward Voltage	V_{SD}	$I_s=30A, V_{GS}=0V$	-	0.92	1.5	V





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Typical Characteristics Curves ($T_J=25^\circ\text{C}$, unless otherwise noted)





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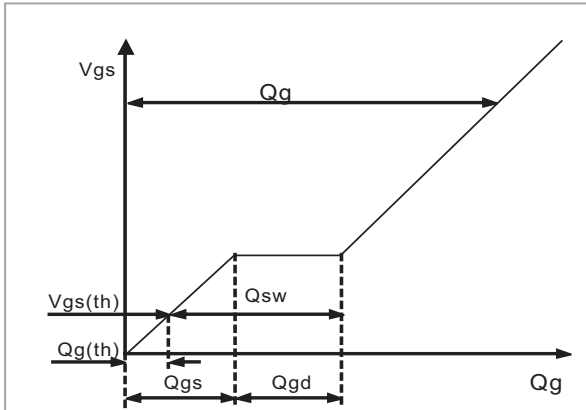


Fig.6 - Gate Charge Waveform

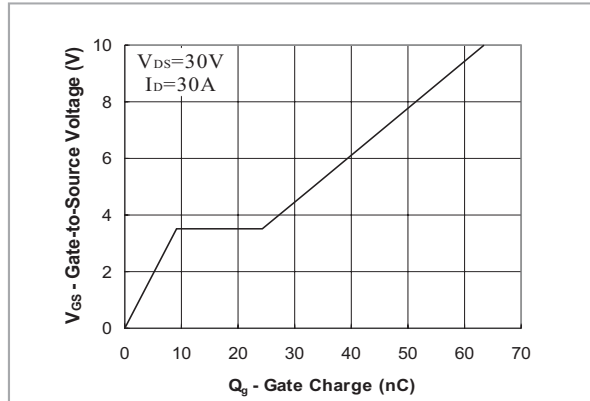


Fig.7 - Gate Charge

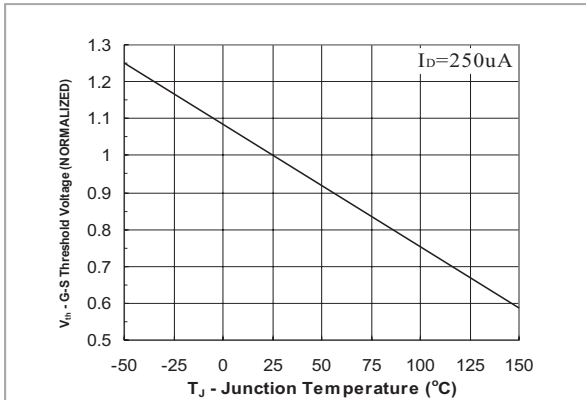


Fig.8 - Threshold Voltage vs Temperature

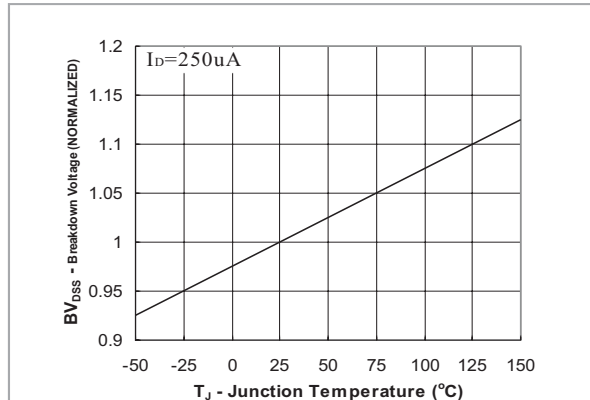


Fig.9 - Breakdown Voltage vs Junction Temperature

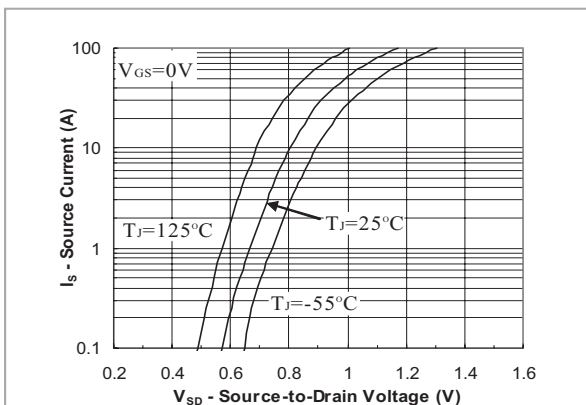


Fig.10 - Source-Drain Diode Forward Voltage

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